

NP75N04YUK

40 V – 75 A – N-channel Power MOS FET
 Application: Automotive

R07DS1004EJ0200
 Rev.2.00
 May 24, 2018

Description

The NP75N04YUK is N-channel MOS Field Effect Transistors designed for high current switching applications.

Features

- Super low on-state resistance
 $R_{DS(on)} = 3.3 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 38 \text{ A)}$
- Non logic level drive type
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	Lead Plating	Packing		Package
NP75N04YUK-E1-AY *1	Pure Sn (Tin)	Tape 2500 p/reel	Taping (E1 type)	8-pin HSON
NP75N04YUK-E2-AY *1			Taping (E2 type)	

Note: *1 Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	40	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 75	A
Drain Current (pulse) *1, 4	$I_{D(pulse)}$	± 300	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	138	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$) *2	P_{T2}	1.0	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$
Repetitive Avalanche Current *3, 4	I_{AR}	35	A
Repetitive Avalanche Energy *3, 4	E_{AR}	123	mJ

Thermal Resistance

Channel to Case Thermal Resistance	$R_{th(ch-C)}$ *4	1.09	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$ *4	150	$^\circ\text{C/W}$

Notes: *1 $T_C = 25^\circ\text{C}$, $P_W \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

*2 Mounted on glass epoxy substrate of 40 mm \times 40 mm \times 1.6 mm with 4% Copper area (35 μm)

*3 $R_G = 25 \Omega$, $V_{GS} = 20 \text{ V} \rightarrow 0 \text{ V}$

*4. Not subject of production test. Verified by design/characterization.

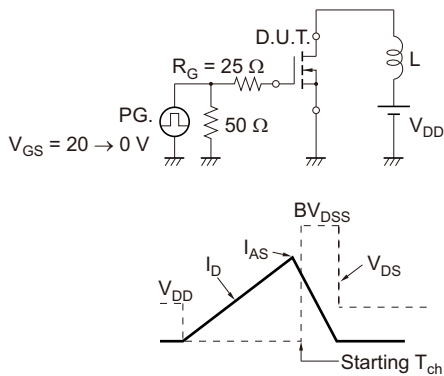
Electrical Characteristics (T_A = 25°C)

Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 40 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}	—	—	±100	nA	V _{GS} = ±20 V, V _{DS} = 0 V
Gate to Source Threshold Voltage	V _{GS(th)}	2.0	3.0	4.0	V	V _{DS} = V _{GS} , I _D = 250 μA
Forward Transfer Admittance *1	y _{fs}	31	62	—	S	V _{DS} = 5 V, I _D = 38 A
Drain to Source On-state Resistance *1	R _{DS(on)}	—	2.6	3.3	mΩ	V _{GS} = 10 V, I _D = 38 A
Input Capacitance *2	C _{iss}	—	3400	5100	pF	V _{DS} = 25 V V _{GS} = 0 V f = 1 MHz
Output Capacitance *2	C _{oss}	—	480	720	pF	
Reverse Transfer Capacitance *2	C _{rss}	—	180	330	pF	
Turn-on Delay Time *2	t _{d(on)}	—	24	48	ns	V _{DD} = 20 V, I _D = 38 A V _{GS} = 10 V R _G = 0 Ω
Rise Time *2	t _r	—	10	25	ns	
Turn-off Delay Time *2	t _{d(off)}	—	60	120	ns	
Fall Time *2	t _f	—	7	17	ns	
Total Gate Charge *2	Q _G	—	58	87	nC	V _{DD} = 32 V V _{GS} = 10 V I _D = 75 A
Gate to Source Charge	Q _{GS}	—	16	—	nC	
Gate to Drain Charge	Q _{GD}	—	15	—	nC	
Body Diode Forward Voltage *1	V _{F(S-D)}	—	0.9	1.5	V	I _F = 75 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}	—	42	—	ns	I _F = 75 A, V _{GS} = 0 V
Reverse Recovery Charge	Q _{rr}	—	51	—	nC	di/dt = 100 A/μs

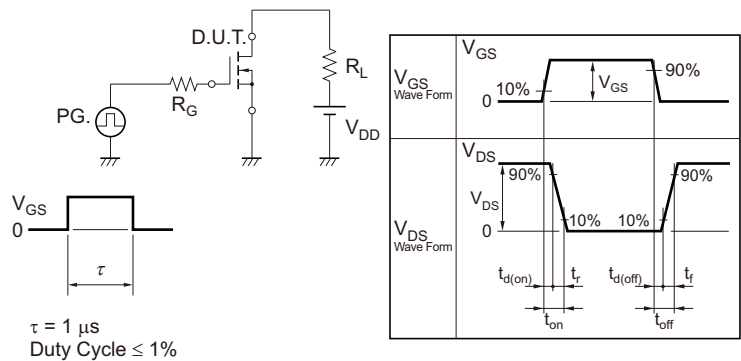
Note: *1 Pulsed test

Note: *2 Not subject of production test. Verified by design/characterization.

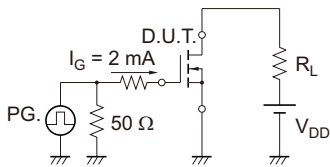
TEST CIRCUIT 1 AVALANCHE CAPABILITY



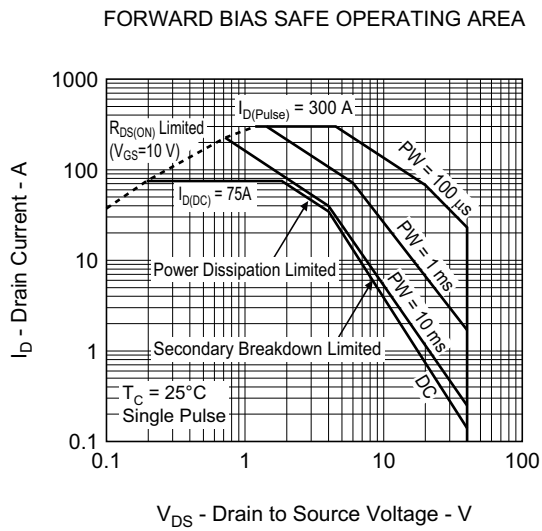
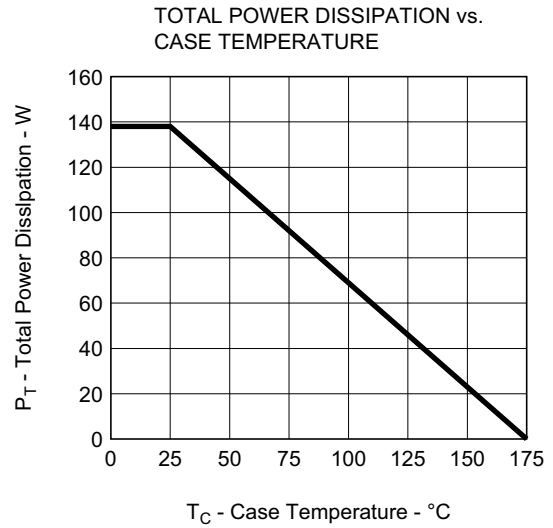
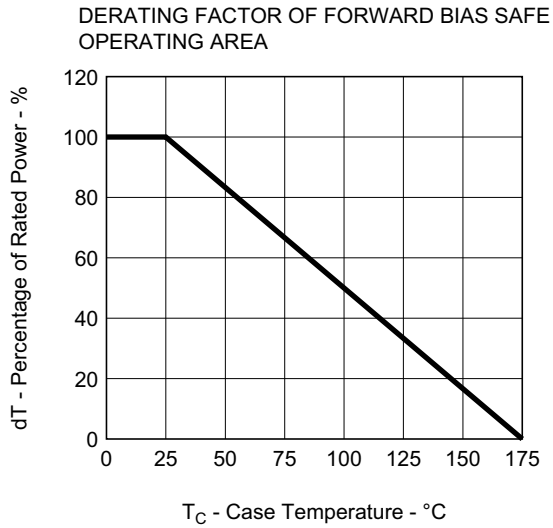
TEST CIRCUIT 2 SWITCHING TIME



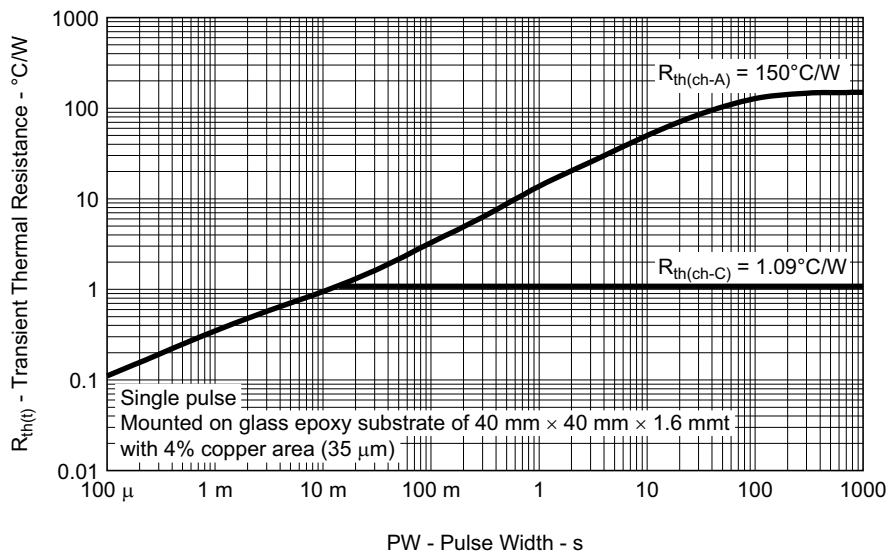
TEST CIRCUIT 3 GATE CHARGE



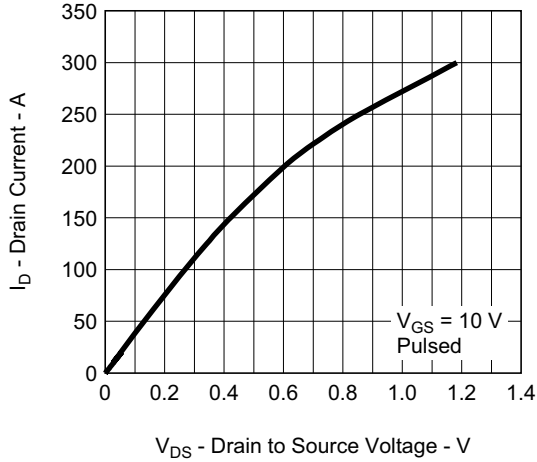
Typical Characteristics (T_A = 25°C)



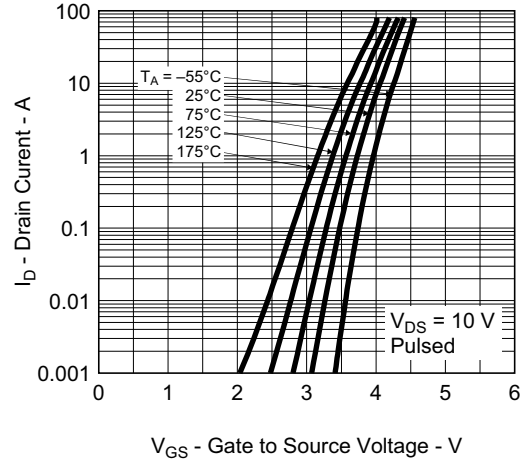
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



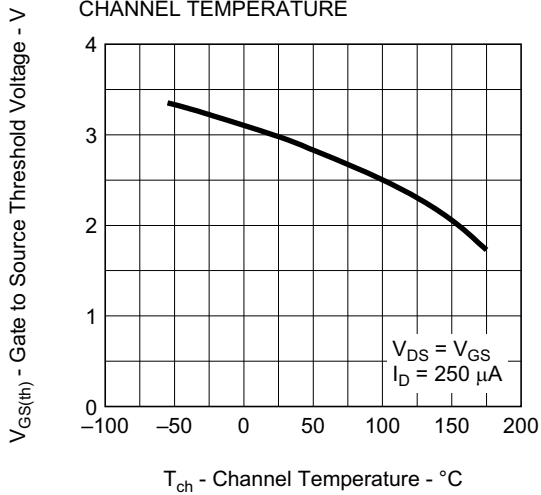
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



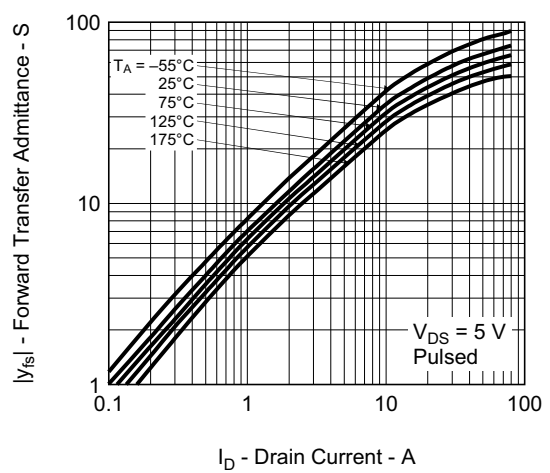
FORWARD TRANSFER CHARACTERISTICS



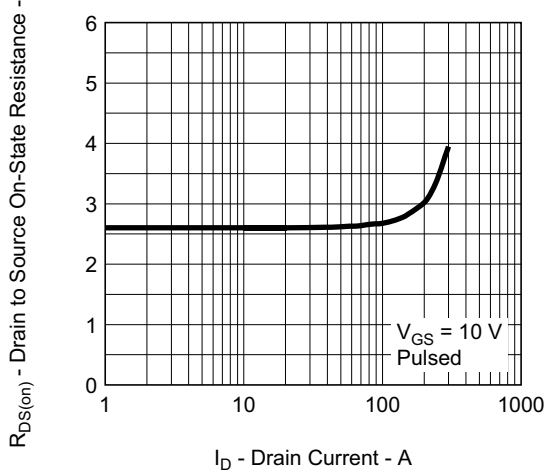
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



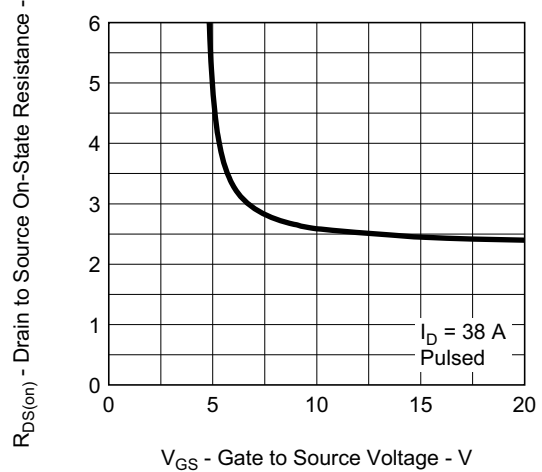
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



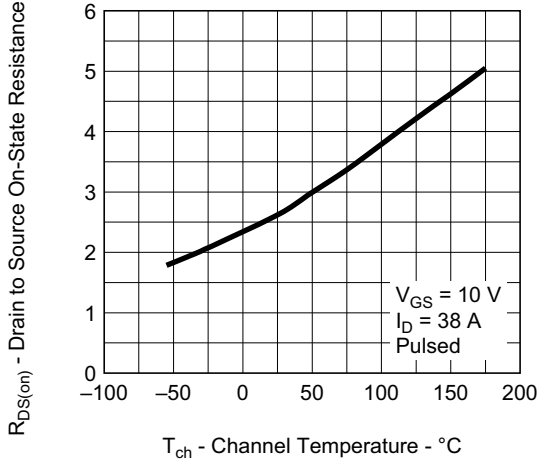
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



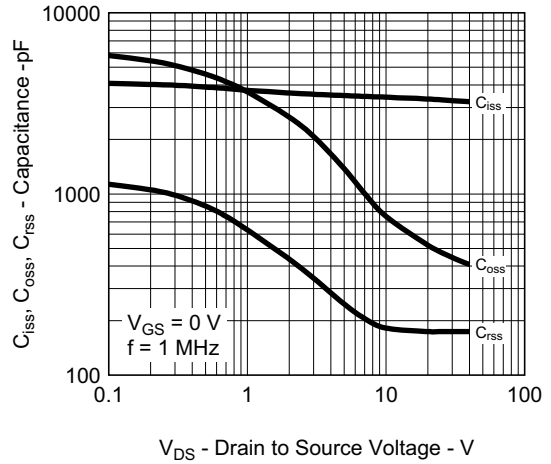
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



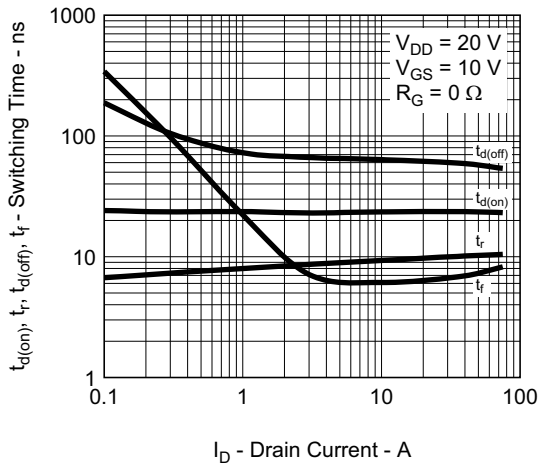
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



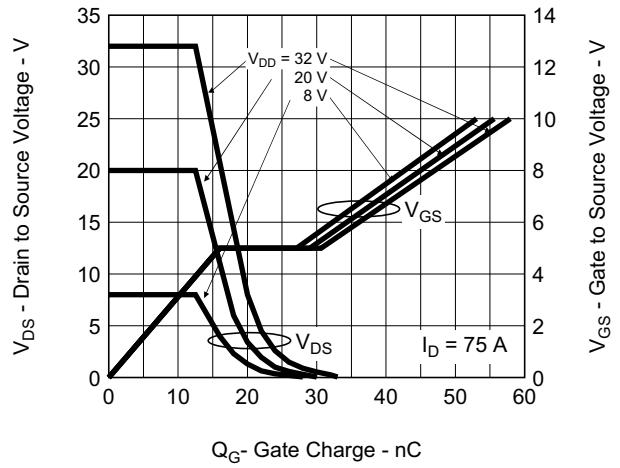
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



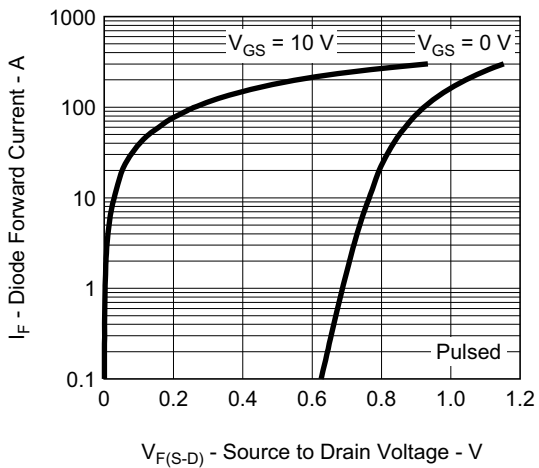
SWITCHING CHARACTERISTICS



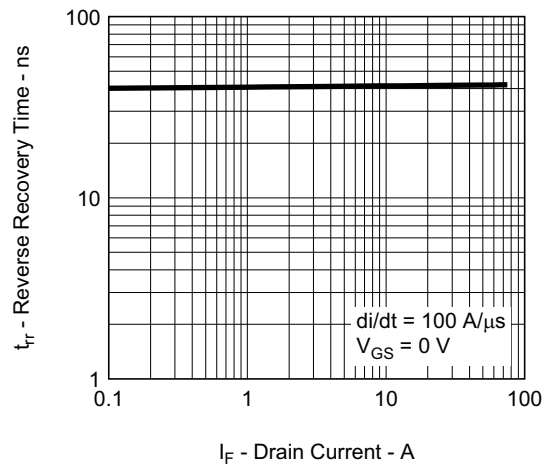
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

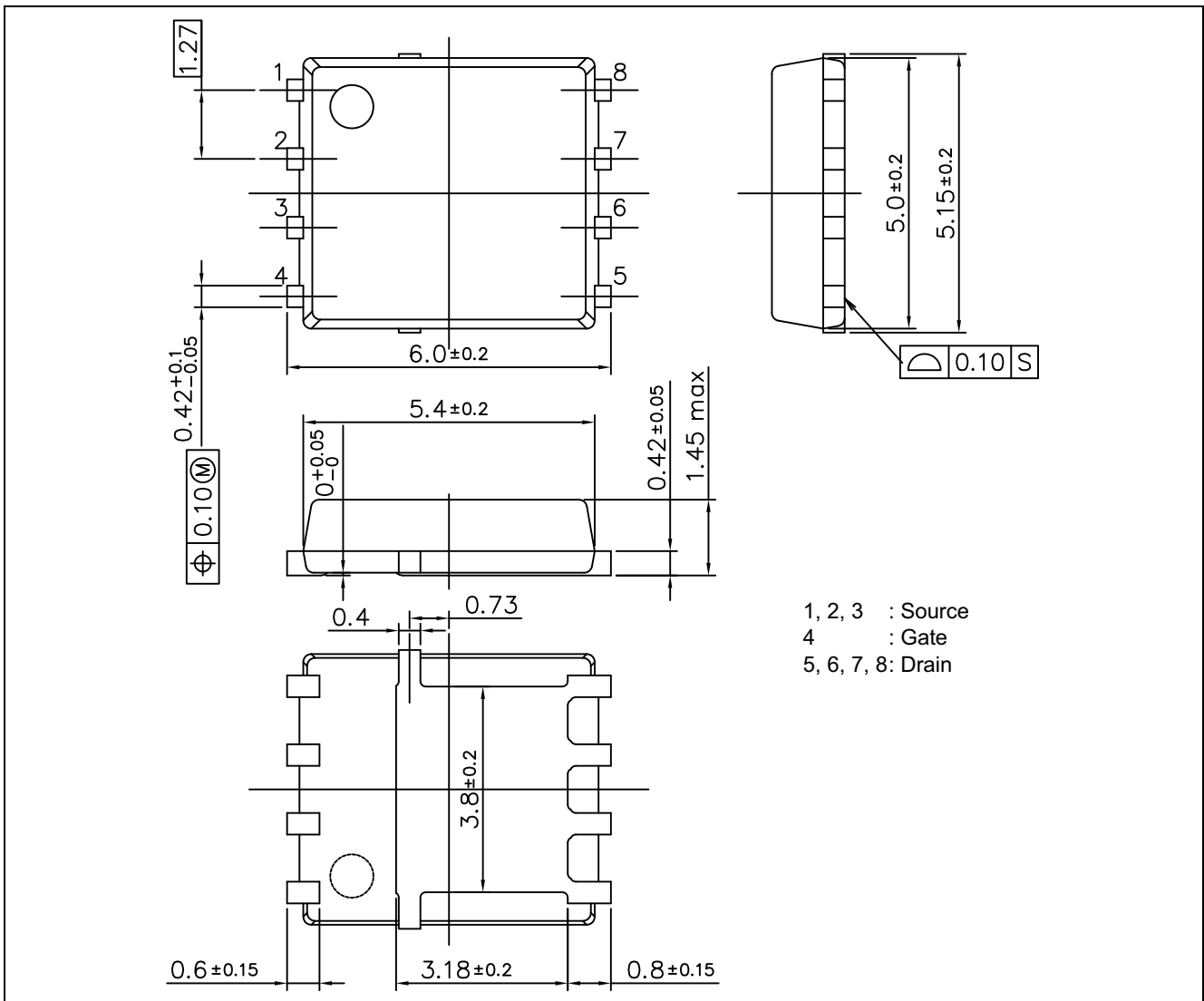


REVERSE RECOVERY TIME vs. DRAIN CURRENT

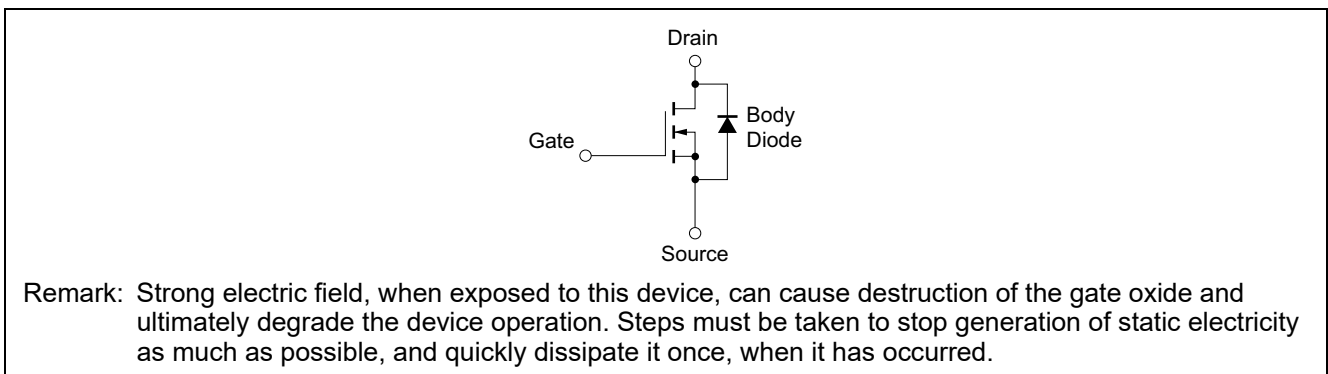


Package Drawing (Unit: mm)

8-pin HSON (Mass: 0.128 g TYP.)



Equivalent Circuit



Revision History	NP75N04YUK Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Feb 08, 2013	—	First Edition Issued
2.00	May 24 ,2018	1	Note 4 was added
		2	Note 2 was added

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(Rev.4.0-1 November 2017)



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Renesas Electronics America Inc.

1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A.
Tel: +1-408-432-8888, Fax: +1-408-434-5351

Renesas Electronics Canada Limited

9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3
Tel: +1-905-237-2004

Renesas Electronics Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.

Room 1709 Quantum Plaza, No.27 ZhichunLu, Haidian District, Beijing, 100191 P. R. China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.

Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, 200333 P. R. China
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited

Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852 2886-9022

Renesas Electronics Taiwan Co., Ltd.

13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.

80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.

Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.

No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.

17F, KAMCO Yangjae Tower, 262, Gangnam-daero, Gangnam-gu, Seoul, 06265 Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5338